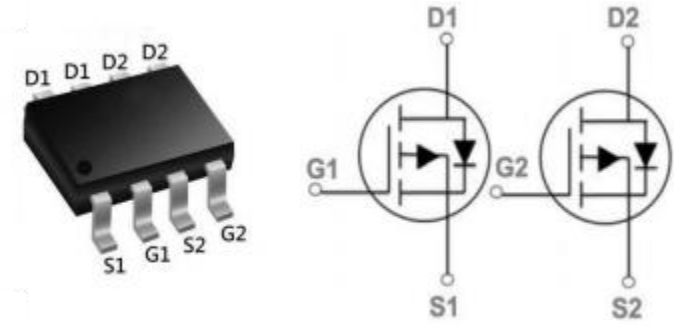
Dual P-Ch 30V Fast Switching MOSFETs

Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

Product Summary

BVDSS	RDSON	ID
-30V	18mΩ	-9.5A

SOP8 Pin Configuration



Description

The XXW4805 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW4805 meet the RoHS and Green Product

Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain- Source Voltage		-30	V
V_{GSS}	Gate- Source Voltage		±20	V
I_D	Continuous Drain Current	T_A= 25℃	-9.5	A
		T_A = 100℃	-5.9	A
I_{DM}	Pulsed Drain Current note1		-36	A
E_{AS}	Single Pulsed Avalanche Energy note2		25	mJ
P_D	Power Dissipation	T_A = 25℃	3.3	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		38	℃/W
T_J , T_{STG}	Operating and Storage Temperature Range		-55 to + 150	℃

Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-30	---	---	V
△BV_{DSS}/△T_J	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.022	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V , I_D=-6A	---	18	25	mΩ
		V_{GS}=-4.5V , I_D=-4A	---	25	42	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-1.0	---	-2.5	V
△$V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-24V , V_{GS}=0V , T_J=25℃	---	---	-1	uA
		V_{DS}=-24V , V_{GS}=0V , T_J=55℃	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-6A	---	17	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	13	---	Ω
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-15V , V_{GS}=-4.5V , I_D=-6A	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	4.8	---	
Q_{gd}	Gate-Drain Charge		---	4.8	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-15V , V_{GS}=-10V , R_G=3.3Ω , I_D=-6A	---	4.6	---	ns
T_r	Rise Time		---	14.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	41	---	
T_f	Fall Time		---	19.6	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	1345	---	pF
C_{oss}	Output Capacitance		---	194	---	
C_{rss}	Reverse Transfer Capacitance		---	158	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	-6.5	A
I_{SM}	Pulsed Source Current[2,5]		---	---	-26	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-6A , dI/dt=100A/μs , T_J=25℃	---	16.3	---	nS
Q_{rr}	Reverse Recovery Charge		---	5.9	---	nC

Note :
1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3. The EAS data shows Max. rating . The test condition is V_{DD}=-25V,V_{GS}=-10V,L=0.1mH, I_{AS}=-38A
4. The power dissipation is limited by 150℃ junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Figure1 : Output Characteristics

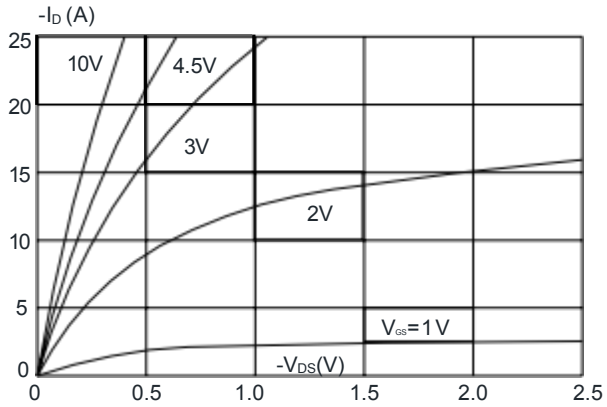


Figure 2 : Typical Transfer Characteristics

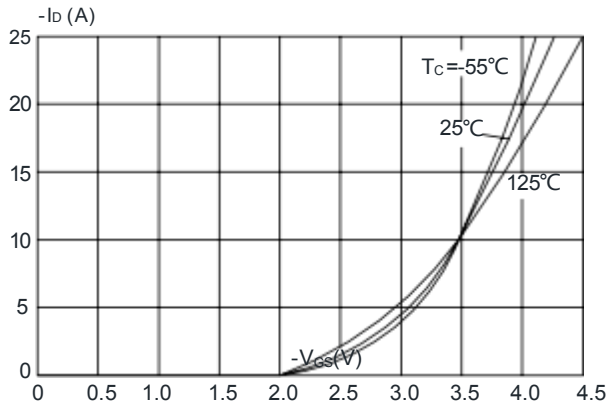


Figure 3: On-resistance vs. Drain Current

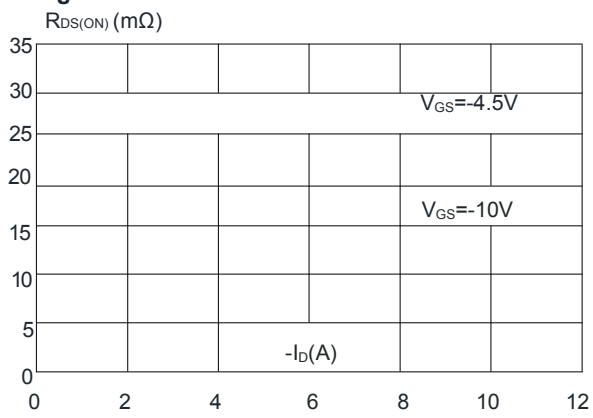


Figure 4 : Body Diode Characteristics

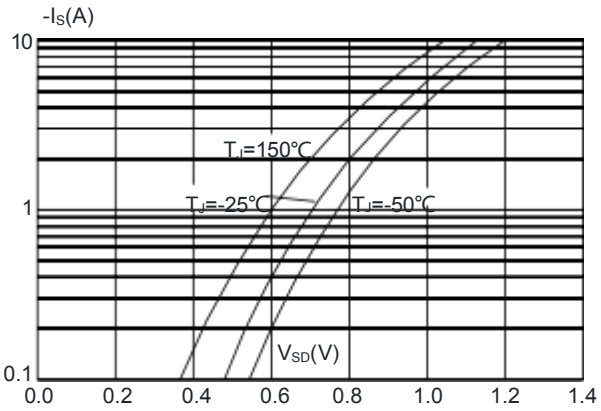


Figure 5: Gate Charge Characteristics

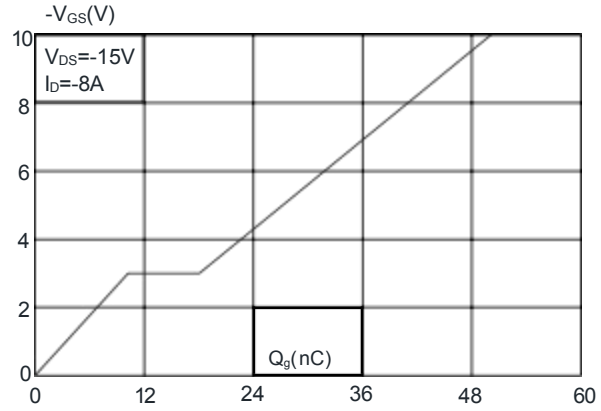


Figure 6: Capacitance Characteristics

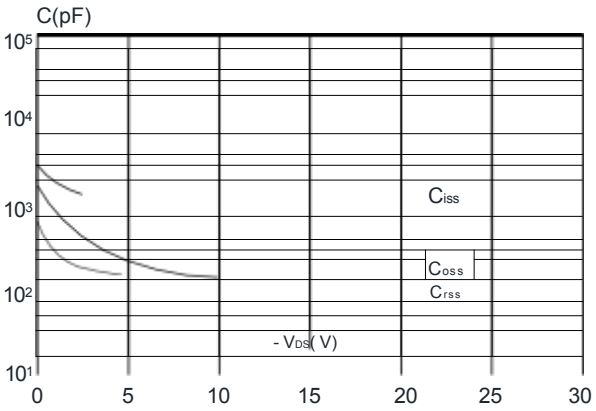


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

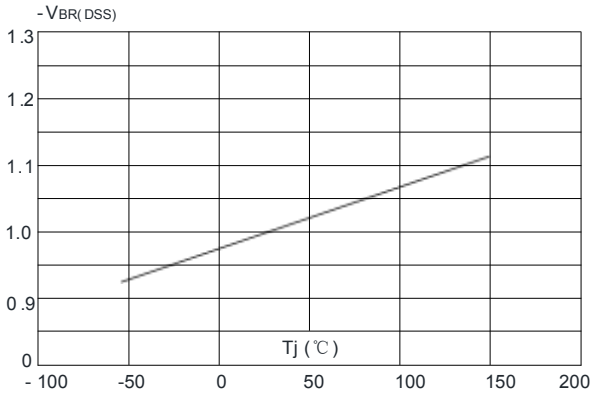


Figure 8: Normalized on Resistance vs. Junction Temperature

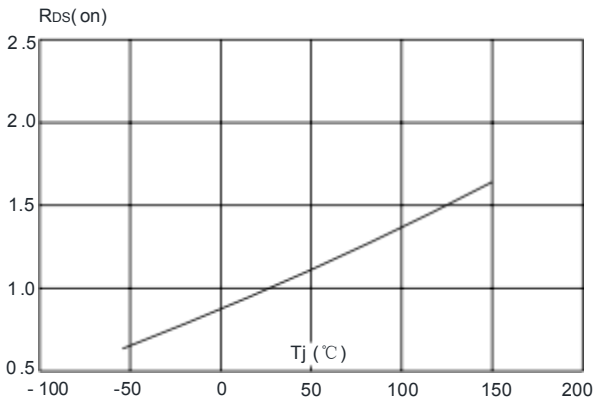


Figure 9: Maximum Safe Operating Area

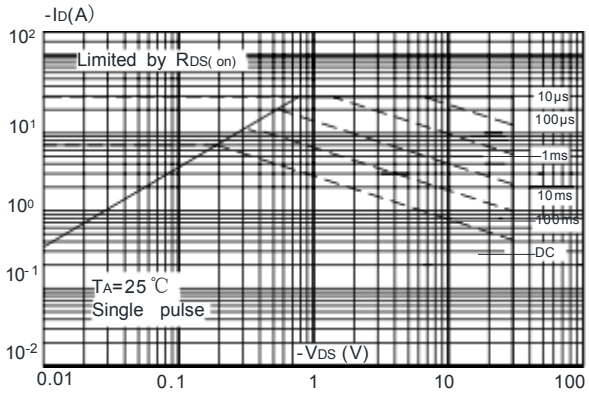
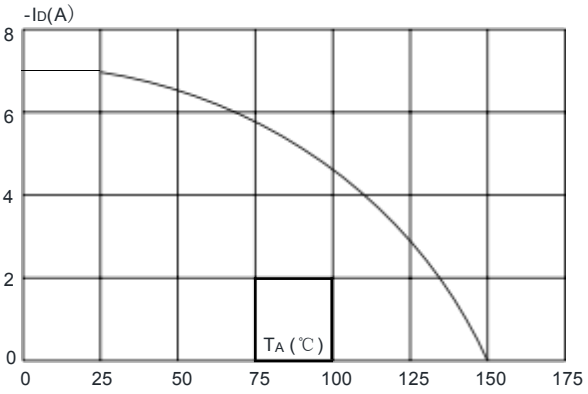
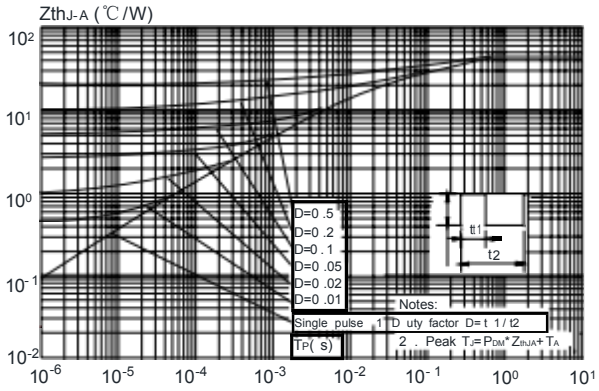


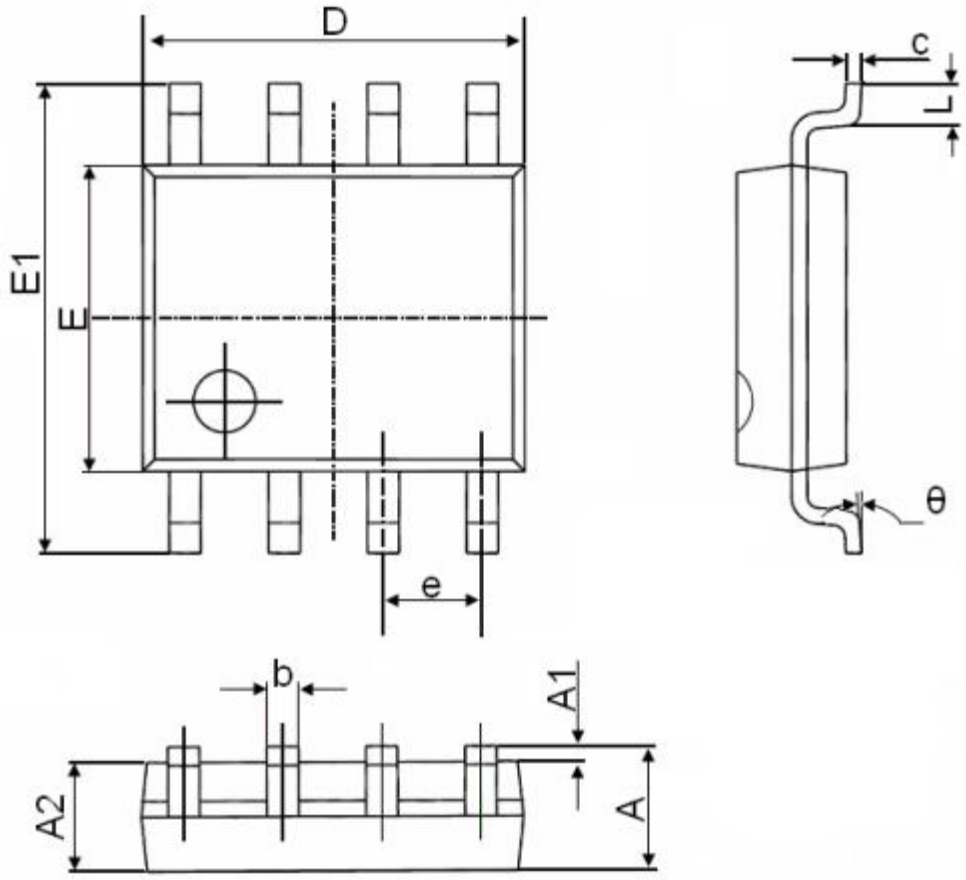
Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature



Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Package Mechanical Data- SOP-8



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		